L Number	Hits	Search Text	DB	Time stamp
6	980	(plasma near etch\$3) and (copper near	USPAT;	2004/09/06 15:09
		plat\$3)	US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
		() 2 () () () () () () () () (IBM_TDB	0004/00/05 == ==
7	699	1 12	USPAT	2004/09/06 15:09
		plat\$3)	,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	2004/00/05 11 15
_	2	("20040063263").PN.	USPAT;	2004/09/06 11:15
			US-PGPUB;	1
			EPO; JPO;	1
			DERWENT; IBM TDB	1
_	1746	438/197	USPAT;	2004/09/02 10:46
	1740	130/13/	US-PGPUB;	2004/05/02 10.40
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	45	438/197 and (backside or (back near side))	USPAT;	2004/09/02 11:23
		,, , , , , , , , , , , , , , , , , , , ,	US-PGPUB;	,,
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
-	17120	(cleaning same wafer) and semiconductor	USPAT;	2004/09/02 11:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2345	((cleaning same wafer) and semiconductor)	USPAT;	2004/09/02 11:37
		and (plasma near etch\$3)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	129	Toledo.xa.	USPAT;	2004/09/02 11:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	259	(wafer near clean\$3) and semiconductor and	IBM_TDB USPAT;	2004/00/04 15:27
_	239	(protective near (flim or layer))	US-PGPUB;	2004/09/04 15:27
		(protective hear (film of layer))	EPO; JPO;	
			DERWENT;	
ļ			IBM TDB	
_	68476	Nakajima.in.	USPAT;	2004/09/04 15:29
		, ,	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	206		USPAT;	2004/09/04 15:30
		semiconductor)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	51	(Nakajima.in. and (protective and	USPAT;	2004/09/04 16:46
		semiconductor)) and CVD	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_	200 mm and water and (=1	IBM_TDB	2004/00/04 16 17
-	0	"300.mm." and wafer and (clean\$3)	USPAT;	2004/09/04 16:47
İ			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	o	"300.mm." near wafer	IBM_TDB	2004/09/04 16:47
-		Jou.mm. Heat water	USPAT; US-PGPUB;	2004/09/04 16:47
}			EPO; JPO;	
ļ			DERWENT;	
			IBM TDB	
	l	<u></u>	T TDM TDB	1

j -	0	"300.mm."	USPAT;	2004/09/04 16:47
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	16321	"300" same wafer	USPAT:	2004/09/04 16:52
	10321	500 Bame warer	US-PGPUB;	2001,03,01 10.32
į			EPO; JPO;	
			DERWENT;	
			IBM TDB	İ
_	6545	("300" same wafer) and clean\$3	USPAT;	2004/09/04 16:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1494	(("300" same wafer) and clean\$3) and (plasma	USPAT;	2004/09/04 16:53
		near etch\$3)	US-PGPUB;	
			EPO; JPO;	1
			DERWENT;	
	E034	(/#200# came wafer) and clean(2) and	IBM_TDB	2004/00/04 16:48
_	5834	(("300" same wafer) and clean\$3) and semiconductor	USPAT;	2004/09/04 16:48
		semiconductor	US-PGPUB; EPO; JPO;	
			DERWENT;	
		,	IBM TDB	ļ
-	1390	((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
		(plasma near etch\$3)) and semiconductor	US-PGPUB;	,,,
		(<u>Farania</u>	EPO; JPO;	1
]			DERWENT;	
1			IBM TDB	į
-	645	(((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)	EPO; JPO;	1
			DERWENT;	
			IBM_TDB	, ,
-	39	((((("300" same wafer) and clean\$3) and	USPAT;	2004/09/04 17:10
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)) and STI	EPO; JPO;	
			DERWENT; IBM TDB	į
_	2722	"300 mm" same wafer	USPAT:	2004/09/04 16:52
	2,22	300 mm Same warer	US-PGPUB;	2004/03/04 10.32
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1456	("300 mm" same wafer) and clean\$3	USPAT;	2004/09/04 16:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(//////////////////////////////////////	IBM_TDB	0004/00/00
-	335	(("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
		(plasma near etch\$3)	US-PGPUB;	
			EPO; JPO;	
1			DERWENT; IBM TDB	
_	330	((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
-	330	(plasma near etch\$3)) and semiconductor	US-PGPUB;	2004/05/04 10:53
		The second of the second of	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	132	(((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/04 16:53
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
[(copper or Cu)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	10	((((("300 mm" same wafer) and clean\$3) and	USPAT;	2004/09/06 15:08
		(plasma near etch\$3)) and semiconductor) and	US-PGPUB;	
		(copper or Cu)) and STI	EPO; JPO;	
			DERWENT;	
			IBM_TDB	l

-	13	(backside near polish\$3) same (mirror) and	USPAT;	2004/09/04 17:15
		semiconductor	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	235	Maydan.in.	USPAT;	2004/09/04 17:15
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	333	Denning.in.	USPAT;	2004/09/06 11:34
			US-PGPUB;	
	· ·		EPO; JPO;	
İ			DERWENT;	
			IBM_TDB	
-	163	Denning.in.	USPAT	2004/09/06 11:37
-	22	Kraft.in. and nitride	USPAT	2004/09/06 11:39
_	6688	copper near plating	USPAT	2004/09/06 11:40
-	10	(copper near plating) and STI	USPAT	2004/09/06 11:40